

FEATURES

- Low capacitance
- Blue enhanced
- High speed
- Low dark current

DESCRIPTION

The **PDB-C201** is a blue enhanced Bi-Cell silicon photodiode used for nulling, centering, or measuring small positional changes packaged in a hermetic TO-5 metal package.

APPLICATIONS

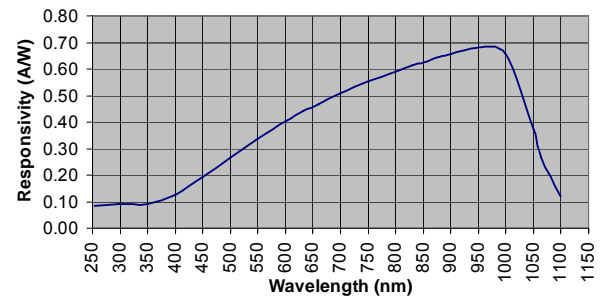
- Emitter Alignment
- Position sensing
- Medical and Industrial

ABSOLUTE MAXIMUM RATING (TA)= 23°C UNLESS OTHERWISE NOTED

| SYMBOL | PARAMETER | MIN | MAX | UNITS |
|------------------|------------------------|-----|------|-------|
| V _{BR} | Reverse Voltage | | 100 | V |
| T _{STG} | Storage Temperature | -55 | +150 | °C |
| T _O | Operating Temperature | -40 | +125 | °C |
| T _S | Soldering Temperature* | | +240 | °C |

* 1/16 inch from case for 3 seconds max.

SPECTRAL RESPONSE



ELECTRO-OPTICAL CHARACTERISTICS RATING (TA)= 23°C UNLESS OTHERWISE NOTED

| SYMBOL | CHARACTERISTIC | TEST CONDITIONS | MIN | TYP | MAX | UNITS |
|-----------------|----------------------------|----------------------------------|-----|---------------------|------|-------|
| I _{SC} | Short Circuit Current | H = 100 fc, 2850 K | 50 | 75 | | μA |
| I _D | Dark Current | V _R = 5V | | 0.5 | 2.0 | nA |
| R _{SH} | Shunt Resistance | V _R = 10 mV | 250 | 500 | | MΩ |
| C _J | Junction Capacitance | V _R = 10 V, f = 1 MHz | | 15 | | pF |
| λ range | Spectral Application Range | Spot Scan | 350 | | 1100 | nm |
| V _{BR} | Breakdown Voltage | I = 10 μA | 50 | 75 | | V |
| NEP | Noise Equivalent Power | V _R = 0V @ λ = Peak | | 1X10 ⁻¹⁴ | | W/√Hz |
| t _r | Response Time** | RL = 50 Ω, V _R = 0 V | | 190 | | nS |
| | | RL = 50 Ω, V _R = 10 V | | 13 | | |

**Response time of 10% to 90% is specified at 660nm wavelength light.

Information in this technical datasheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject to change without notice.